

5/20/14

Page 1 of 2

FORM PTO-1449

INFORMATION DISCLOSURE STATEMENT

ATTY. DOCKET NO.

1875.0220001

APPLICATION NO.

To Be Assigned

FIRST NAMED INVENTOR

Vincent Chen

FILING DATE

Herewith

ART UNIT

To Be Assigned

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE
<i>D</i>	AA1	4,173,791	11/1979	Bell, Antony G.	<i>—</i>	<i>—</i>	
<i>D</i>	AB1	4,499,557	02/1985	Holmberg <i>et al.</i>	<i>—</i>	<i>—</i>	
<i>2</i>	AC1	5,163,180	11/1992	Eltoukhy <i>et al.</i>	<i>—</i>	<i>—</i>	
<i>D</i>	AD1	5,480,828	01/1996	Hsu <i>et al.</i>	<i>—</i>	<i>—</i>	
<i>D</i>	AE1	5,742,555	04/1998	Marr <i>et al.</i>	<i>—</i>	<i>—</i>	
<i>D</i>	AF1	5,748,025	05/1998	Ng <i>et al.</i>	<i>—</i>	<i>—</i>	
<i>D</i>	AG1	5,834,824	11/1998	Shepherd <i>et al.</i>	<i>—</i>	<i>—</i>	
<i>D</i>	AH1	5,886,392	03/1999	Schuegraf	<i>—</i>	<i>—</i>	
<i>D</i>	AI1	5,949,712	09/1999	Rao <i>et al.</i>	<i>—</i>	<i>—</i>	
<i>2</i>	AJ1	6,044,012	03/2000	Rao <i>et al.</i>	<i>—</i>	<i>—</i>	
<i>D</i>	AK1	6,096,580	08/2000	Iyer <i>et al.</i>	<i>—</i>	<i>—</i>	

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION
	AL1						Yes
							No
	AM1						Yes
							No
	AN1						Yes
							No
	AO1						Yes
							No
	AP1						Yes
							No

OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

<i>D</i>	AR	1	Clark, Lawrence T., "A High-Voltage Output Buffer Fabricated on a 2V CMOS Technology," <i>Symposium on VLSI Circuits Digest of Technical Papers</i> , pp. 61-62, 1999.				
<i>D</i>	AS	1	International Search Report for PCT/US01/48853, 5 pages, July 31, 2002.				
<i>D</i>	AT	1	Schroder, Dieter K., "Semiconductor Material and Device Characterization," Fig. E6.5(a), Oxide failure modes, John Wiley & Sons, Inc., 2 nd Edition, p. 391, 1998.				

EXAMINER

DATE CONSIDERED

2/5/08

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

5/20/04

FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT	ATTY. DOCKET NO. 1875.0220001	APPLICATION NO. To Be Assigned
	FIRST NAMED INVENTOR Vincent Chen	
	FILING DATE Herewith	ART UNIT To Be Assigned

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE
<i>2</i>	AA2	6,096,610	08/2000	Alavi <i>et al.</i>			
<i>2</i>	AB2	6,184,726 B1	02/2001	Haebler <i>et al.</i>			06/29/1999
<i>2</i>	AC2	6,266,269 B1	07/2001	Karp <i>et al.</i>			06/07/2000
<i>2</i>	AD2	6,351,425 B1	02/2002	Porter, Stephen R.			12/07/2000
<i>2</i>	AE2	6,477,094 B2	11/2002	Kim <i>et al.</i>			12/18/2000
<i>2</i>	AF2	6,549,458 B1	04/2003	Rao <i>et al.</i>			10/25/2001
	AG2						
	AH2						
	AI2						
	AJ2						
	AK2						

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION
	AL2						Yes No
	AM2						Yes No
	AN2						Yes No
	AO2						Yes No
	AP2						Yes No

OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

<i>2</i>	AR	<u>2</u>	Schroder, Dieter K., "Semiconductor Material and Device Characterization," Fig. 6.40, Charge-to-breakdown as a function of oxide thickness, John Wiley & Sons, Inc., 2 nd Edition, p. 397, 1998.
<i>2</i>	AS	<u>2</u>	Shi, Y., <i>et al.</i> , "Polarity-Dependent Tunneling Current and Oxide Breakdown in Dual-Gate CMOSFET's," <i>IEEE Electron Device Letters</i> , Volume 19, No. 10, pp. 391-393, October 1998.
	AT	<u>2</u>	

EXAMINER <i>[Signature]</i>	DATE CONSIDERED <i>2/5/00</i>
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.	

FIRST SUPPLEMENTAL
INFORMATION DISCLOSURE STATEMENT

APPLICATION NO.
10/849,295

FILING DATE
May 20, 2004

ART UNIT
2815

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE
<i>PD</i>	AG2	6,445,619 B1	09/2002	Mihnea <i>et al.</i>			08/01/2001
<i>PD</i>	AH2	6,566,189 B2	05/2003	Joo <i>et al.</i>			07/02/2001

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION
							Yes
							No
							Yes
							No
							Yes
							No
							Yes
							No
							Yes
							No

The diagram consists of a 3x4 grid of squares. A diagonal line starts at the bottom-left corner of the first square and extends to the top-right corner of the last square, passing through the center of the grid.

DATE CONSIDERED

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